TOSHIBA Transistor Silicon NPN Epitaxial Type

## 2SC5819

# High-Speed Switching Applications DC-DC Converter Applications

- High DC current gain:  $h_{FE}$  = 400 to 1000 (I<sub>C</sub> = 0.15 A)
- Low collector-emitter saturation voltage: VCE (sat) = 0.12 V (max)
- High-speed switching:  $t_f = 45$  ns (typ.)

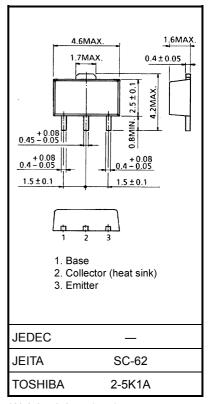
#### Maximum Ratings (Ta = 25°C)

| Characteristics             |          | Symbol           | Rating     | Unit |  |
|-----------------------------|----------|------------------|------------|------|--|
| Collector-base voltage      |          | V <sub>CBO</sub> | 40         | V    |  |
| Collector-emitter voltage   |          | V <sub>CEX</sub> | 30         | V    |  |
| Collector-emitter voltage   |          | V <sub>CEO</sub> | 20         | V    |  |
| Emitter-base voltage        |          | V <sub>EBO</sub> | 7          | V    |  |
| Collector current           | DC       | Ic               | 1.5        | Α    |  |
|                             | Pulse    | I <sub>CP</sub>  | 2.5        |      |  |
| Base current                |          | ΙΒ               | 150        | mA   |  |
| Collector power dissipation | t = 10 s | PC               | 2.0        | W    |  |
|                             | DC       | (Note 1)         | 1.0        |      |  |
| Junction temperature        |          | Tj               | 150        | °C   |  |
| Storage temperature range   |          | T <sub>stg</sub> | -55 to 150 | °C   |  |

Note 1: Mounted on FR4 board (glass epoxy, 1.6 mm thick, Cu area: 645 mm²)

#### **Industrial Applications**

Unit: mm

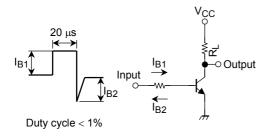


Weight: 0.05 g (typ.)

#### **Electrical Characteristics (Ta = 25°C)**

| Characteristics                      |              | Symbol                | Test Condition  | Min | Тур. | Max  | Unit |
|--------------------------------------|--------------|-----------------------|---|-----|------|------|------|
| Collector cut-off current            |              | I <sub>CBO</sub>      | $V_{CB} = 40 \text{ V}, I_E = 0$                        | _   | _    | 100  | nA   |
| Emitter cut-off current              |              | I <sub>EBO</sub>      | $V_{EB} = 7 \text{ V, } I_{C} = 0$                      | _   | _    | 100  | nA   |
| Collector-emitter breakdown voltage  |              | V (BR) CEO            | $I_C = 10 \text{ mA}, I_B = 0$                          | 20  | _    | _    | V    |
| DC current gain                      |              | h <sub>FE</sub> (1)   | $V_{CE} = 2 \text{ V}, I_{C} = 0.15 \text{ A}$          | 400 | _    | 1000 |      |
|                                      |              | h <sub>FE</sub> (2)   | $V_{CE} = 2 \text{ V}, I_{C} = 0.5 \text{ A}$           | 200 | _    | _    |      |
| Collector-emitter saturation voltage |              | V <sub>CE</sub> (sat) | $I_C = 0.5 \text{ A}, I_B = 10 \text{ mA}$              | _   | _    | 0.12 | V    |
| Base-emitter saturation voltage      |              | V <sub>BE (sat)</sub> | $I_C = 0.5 \text{ A}, I_B = 10 \text{ mA}$              | _   | _    | 1.10 | V    |
| Collector output capacitance         |              | C <sub>ob</sub>       | V <sub>CB</sub> = 10 V, I <sub>E</sub> = 0, f = 1 MHz   | _   | 18   | _    | pF   |
| Switching time                       | Rise time    | t <sub>r</sub>        | See Figure 1 circuit diagram.                           | _   | 43   | _    |      |
|                                      | Storage time | t <sub>stg</sub>      | $V_{CC} \simeq 12 \text{ V}, \text{ R}_{L} = 24 \Omega$ | _   | 295  | _    | ns   |
|                                      | Fall time    | t <sub>f</sub>        | $I_{B1} = -I_{B2} = 17 \text{ mA}$                      | _   | 45   | _    |      |

### Marking



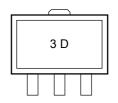
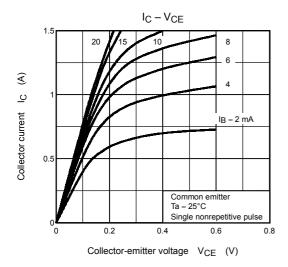
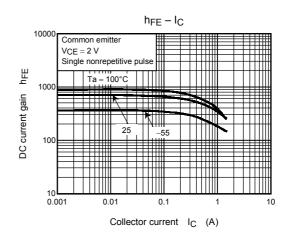
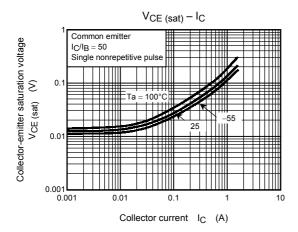
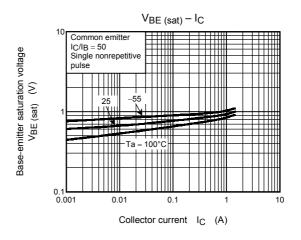


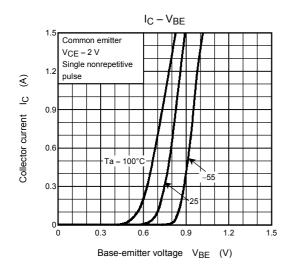
Figure 1 Switching Time Test Circuit & Timing Chart



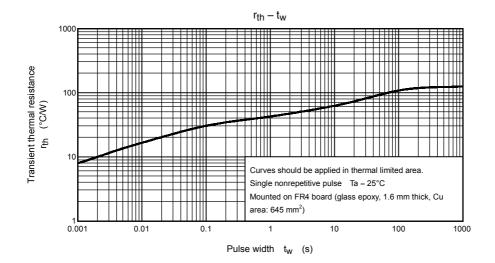


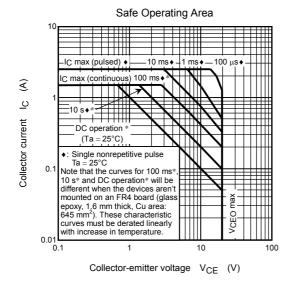






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